MT160CB-T2

RoHS COMPLIANT

Thyristor/Diode Modules

V_{RRM} / V_{DRM}

Module Type

Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_D	Output Current(D.C.)	Tc=85	160	A
I_{FSM}	Surge forward current	t=10mS Tvj =45	5400	A
i^2t	Circuit Fusing Consideration		145000	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
Tvj	Operating Junction Temperature		-40 to +125	
Tstg	Storage Temperature		-40 to +125	
Mt	Mounting Torque	To terminals(M6)	3±15%	Nm
Ms		To heatsink(M6)	5±15%	Nm
Weight	Module Approximately		165	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.085	/W
Rth(c-s)	Thermal Impedance, max.	Case to Heatsink	0.05	/W

Electrical Characteristics

Thyristor

Maximum Ratings

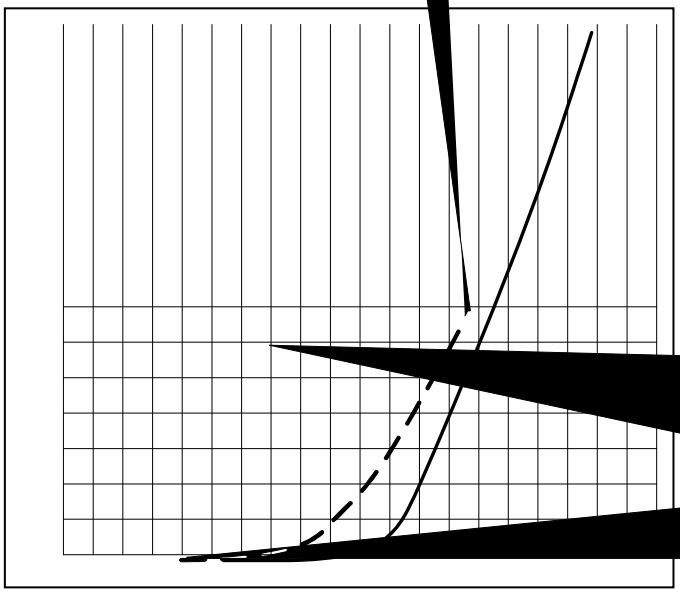
Symbol	Item	Conditions	Values	Units
I_{TAV}	Average On-State Current	Sine 180°;Tc=85	160	A
I_{TSM}	Surge On-State Current	T_{VJ}=45 t=10ms, sine T_{VJ}=125 t=10ms, sine	5400 5000	A
i^2t	Circuit Fusing Consideration	T_{VJ}=45 t=10ms, sine T_{VJ}=125 t=10ms, sine	145000 125000	A2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
Tvj	Operating Junction Temperature		-40 to +125	
Tstg	Storage Temperature		-40 to +125	
Mt	Mounting Torque	To terminals(M6)	3	

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.17	/W
Rth(c-s)	Thermal Impedance, max.	Case to Heatsink	0.10	/W

Electrical Characteristics

Performance Curves



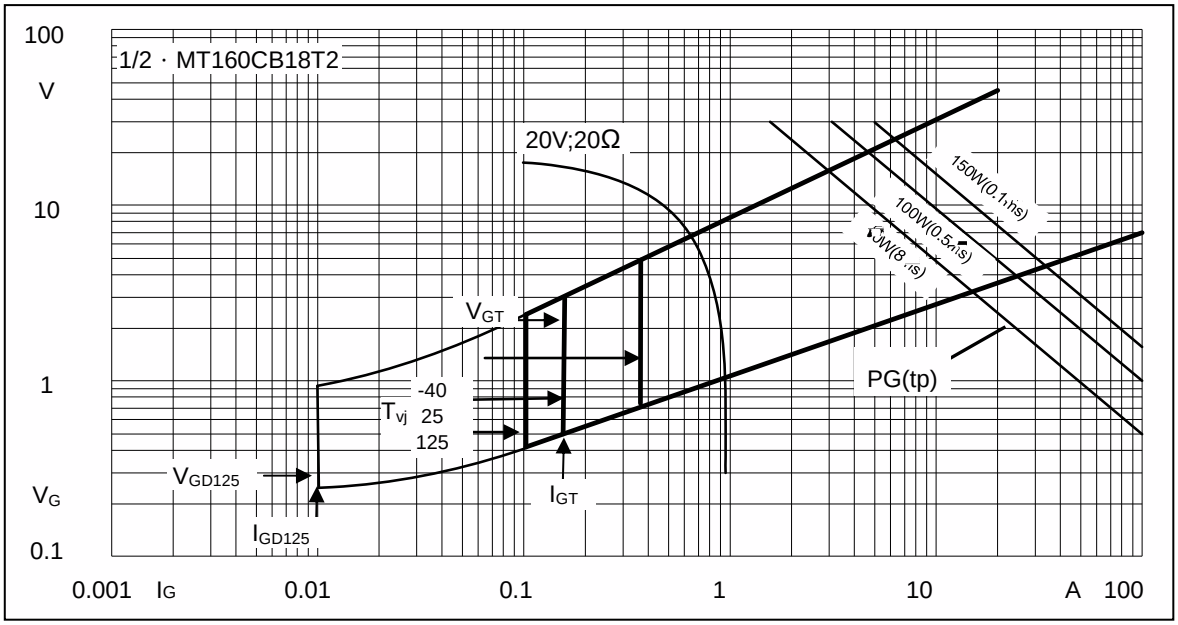
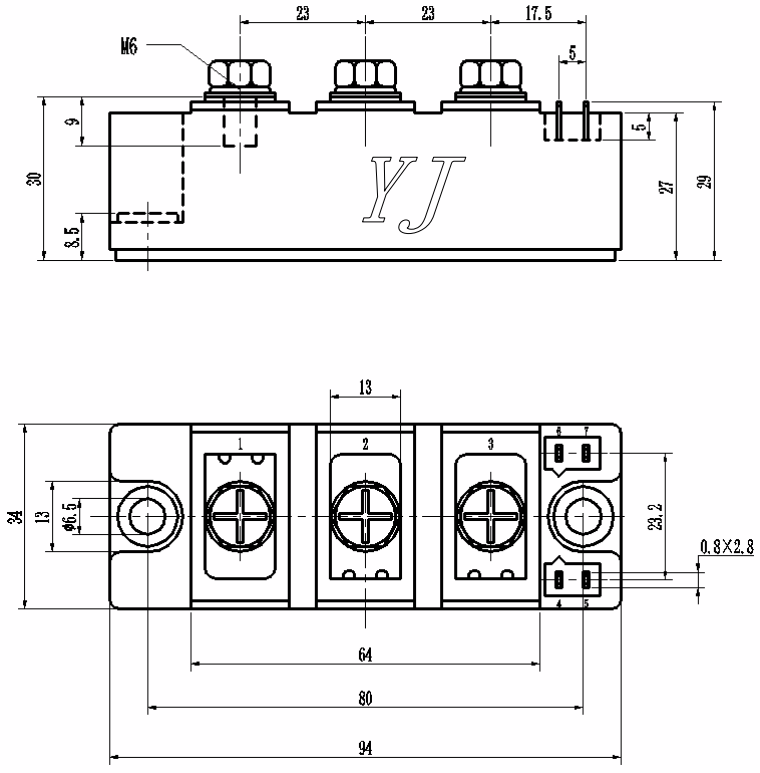


Fig6. Gate trigger Characteristics

Package Outline Information

CASE: T2



Dimensions in mm